Ordering number : ENN6595

Schottky Barrier Diode

SBS804

15V, 1A Rectifier

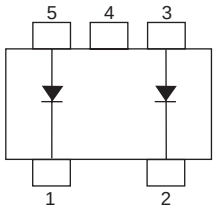
Applications

- High frequency rectification (switching regulators, converters, choppers).

Features

- Low forward voltage (I_F=0.5A, V_F max=0.35V) (I_F=1.0A, V_F max=0.4V).
- Short reverse recovery time(t_{rr} max.=15ns).
- Composite type with 2 low VF SBDs in one package, facilitating high-density mounting.
- The SBS804 is composed of 2 chips that are equivalent to the SBS004.

Electrical Connection

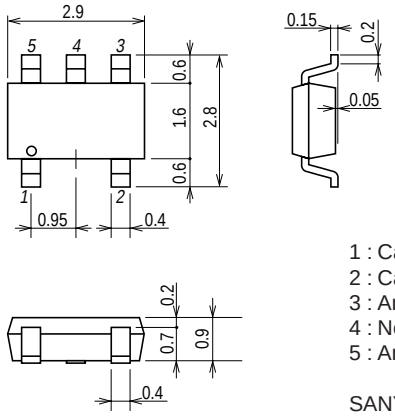


1 : Cathode
2 : Cathode
3 : Anode
4 : No Contact
5 : Anode

Package Dimensions

unit : mm
1294

[SBS804]



1 : Cathode
2 : Cathode
3 : Anode
4 : No Contact
5 : Anode

SANYO : CPH5

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		15	V
Nonrepetitive Peak Reverse Surge Voltage	V_{RSM}		15	V
Average Output Current	I_O		1	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	10	A
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=1mA	15			V
Forward Voltage	V_F1	I_F=0.5A		0.30	0.35	V
	V_F2	I_F=1A		0.35	0.40	V
Reverse Current	I_R	V_R=6V			500	μA
Interterminal Capacitance	C	V_R=10V, f=1MHz		42		pF
Reverse Recovery Time	t_{rr}	I_F=I_R=100mA, See specified Test Circuit.			15	ns
Therminal Resistance	Rth(j-a)	Mounted on a ceramic board (600mm²×0.8mm)		110		°C/W

Marking : SC

Switching Time Test Circuit